



PSMNR90-40YLH

N-channel 40 V, 0.94 mΩ, 300 A logic level MOSFET in LFAK56E using NextPower-S3 Schottky-Plus technology

26 April 2019

Product data sheet

1. General description

300 Amp, logic level gate drive N-channel enhancement mode MOSFET in 175 °C LFAK56E package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high performance power switching applications.

2. Features and benefits

- 300 A continuous $I_{D(max)}$
- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q_{RR} , Q_G and Q_{GD} for high system efficiency and low EMI designs
- Schottky-Plus body-diode, gives soft switching without the associated high I_{DSS} leakage
- Strong linear-mode / SOA rating
- Optimised for 4.5 V gate drive utilising NextPower-S3 Superjunction technology
- High reliability LFAK (Power SO8) package, with copper-clip and solder die attach, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints for ultimate reliability
- Low parasitic inductance and resistance

3. Applications

- High-performance synchronous rectification
- DC-to-DC converters
- High performance and high efficiency server power supply
- Brushless DC motor control
- Battery protection
- Load-switch and eFuse

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|------------------------------------------------------------------------------------------------|-----|------|------|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | - | 40 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2 | [1] | - | 300 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; Fig. 1 | - | - | 333 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 4.5\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 0.97 | 1.2 | mΩ |
| | | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 0.76 | 0.94 | mΩ |
| Dynamic characteristics | | | | | | |

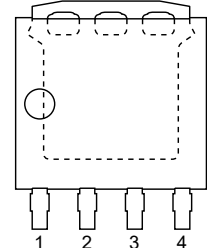
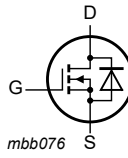
N-channel 40 V, 0.94 mΩ, 300 A logic level MOSFET in LPAK56E using NextPower-S3 Schottky-Plus technology

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------|----------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| Q_{GD} | gate-drain charge | $I_D = 25 \text{ A}$; $V_{DS} = 20 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; Fig. 12 ; Fig. 13 | - | 13 | 26 | nC |
| $Q_{G(\text{tot})}$ | total gate charge | | - | 54 | 76 | nC |

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1 | S | source |  <p>LPAK56E; Power-SO8 (SOT1023)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|--------------------|--------------------------------------------------------------------------------|---------|
| | Name | Description | Version |
| PSMNR90-40YLH | LPAK56E; Power-SO8 | plastic, single-ended surface-mounted package (LPAK56); 4 leads; 1.27 mm pitch | SOT1023 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|--------------|
| PSMNR90-40YLH | H90L40J |

8. Limiting values

Table 5. Limiting values

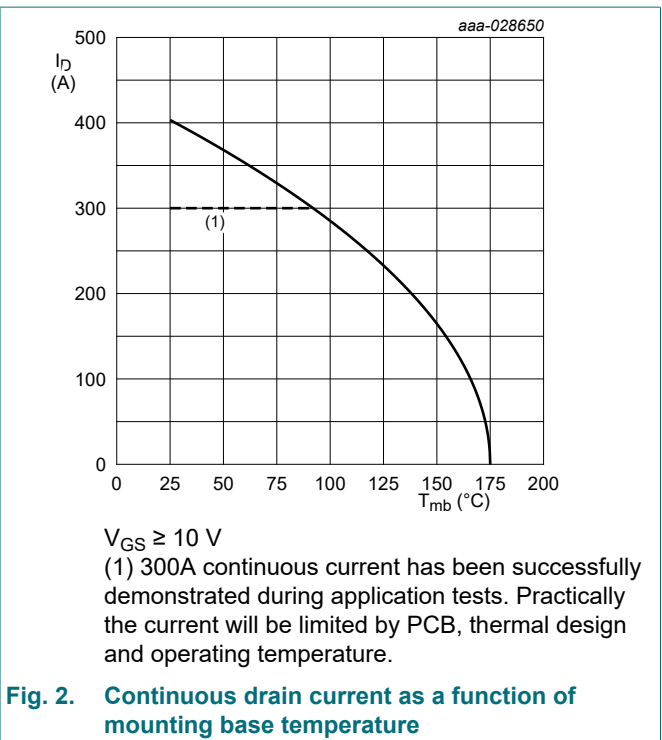
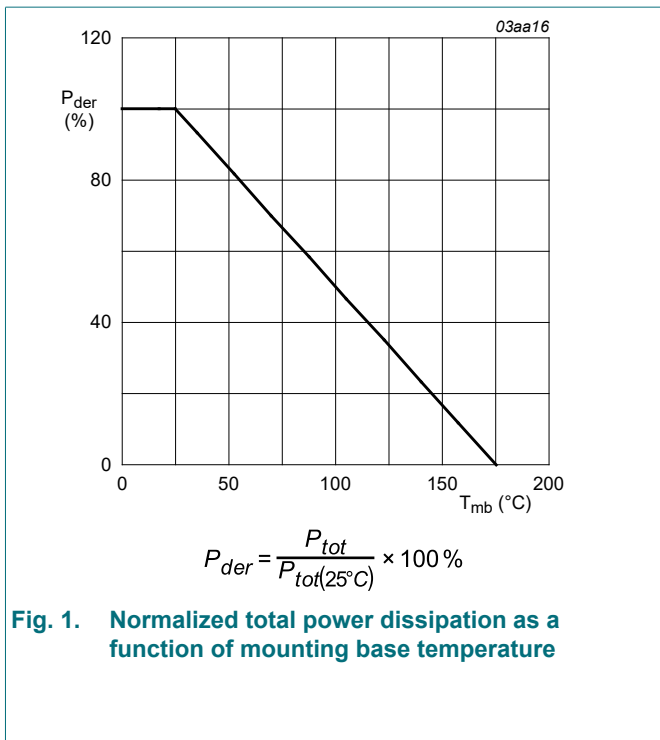
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------------------------------------------------------------------|-----|-----|------|
| V_{DS} | drain-source voltage | $25 \text{ °C} \leq T_j \leq 175 \text{ °C}$ | - | 40 | V |
| V_{DSM} | peak drain-source voltage | $t_p \leq 20 \text{ ns}$; $f \leq 500 \text{ kHz}$; $E_{DS(AL)} \leq 200 \text{ nJ}$; pulsed | - | 45 | V |
| V_{DGR} | drain-gate voltage | $25 \text{ °C} \leq T_j \leq 175 \text{ °C}$; $R_{GS} = 20 \text{ k}\Omega$ | - | 40 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{\text{mb}} = 25 \text{ °C}$; Fig. 1 | - | 333 | W |
| I_D | drain current | $V_{GS} = 10 \text{ V}$; $T_{\text{mb}} = 25 \text{ °C}$; Fig. 2 | [1] | 300 | A |
| | | $V_{GS} = 10 \text{ V}$; $T_{\text{mb}} = 100 \text{ °C}$; Fig. 2 | - | 285 | A |

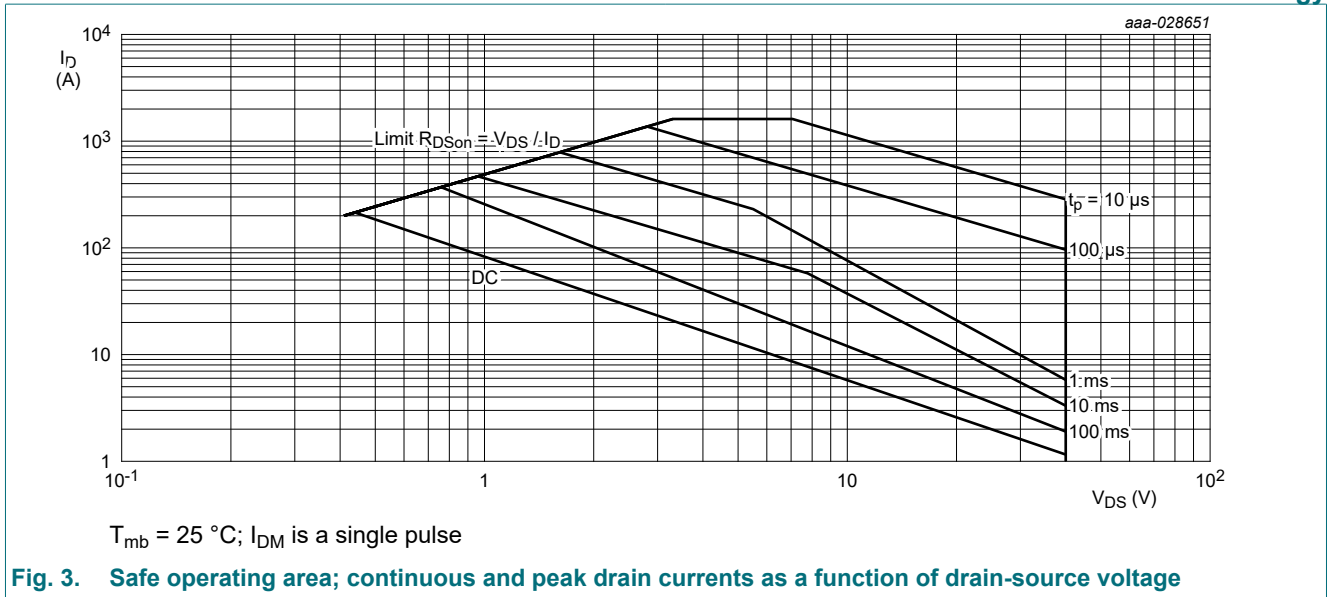
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| Symbol | Parameter | Conditions | Min | Max | Unit | |
|-----------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------------------|----|
| I_{DM} | peak drain current | pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 3 | - | 1613 | A | |
| T_{stg} | storage temperature | | -55 | 175 | $^\circ\text{C}$ | |
| T_j | junction temperature | | -55 | 175 | $^\circ\text{C}$ | |
| $T_{sld(M)}$ | peak soldering temperature | | - | 260 | $^\circ\text{C}$ | |
| Source-drain diode | | | | | | |
| I_S | source current | $T_{mb} = 25 \text{ }^\circ\text{C}$ | - | 278 | A | |
| I_{SM} | peak source current | pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$ | - | 1613 | A | |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 83 \text{ A}$; $V_{sup} \leq 40 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; unclamped; $t_p = 0.27 \text{ ms}$ | [2] | - | 577 | mJ |
| | | $I_D = 25 \text{ A}$; $V_{sup} \leq 40 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; unclamped; $t_p = 4.1 \text{ ms}$ | [2] | - | 2706 | mJ |
| I_{AS} | non-repetitive avalanche current | $V_{sup} \leq 40 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; $R_{GS} = 50 \Omega$ | [2] | - | 190 | A |

- [1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test



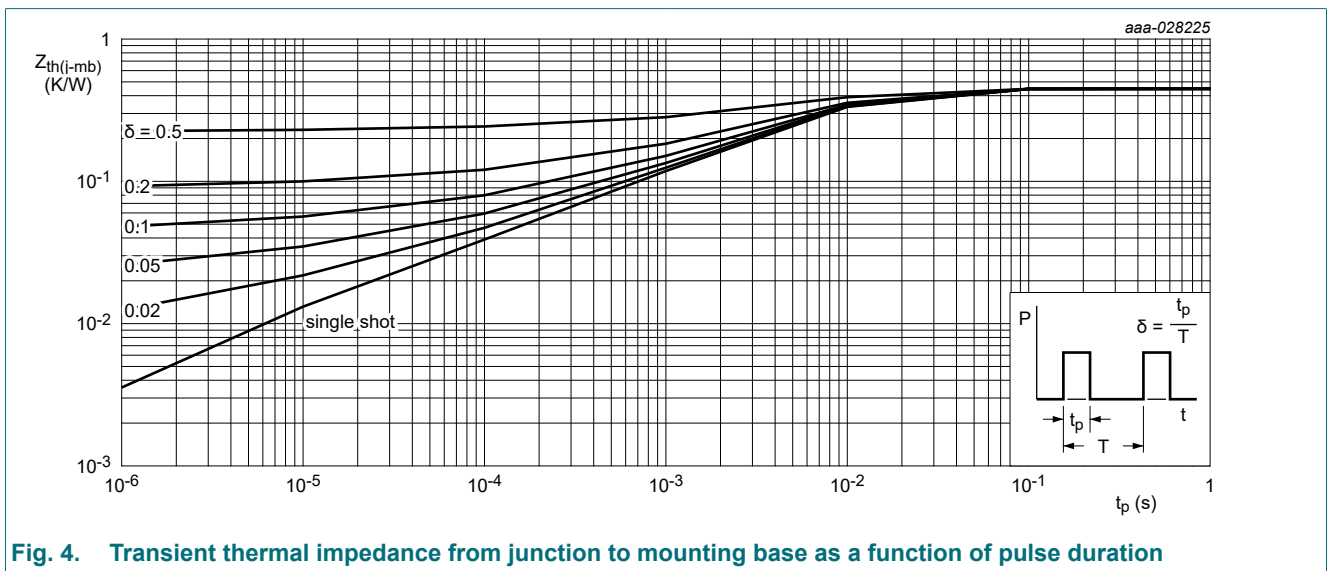
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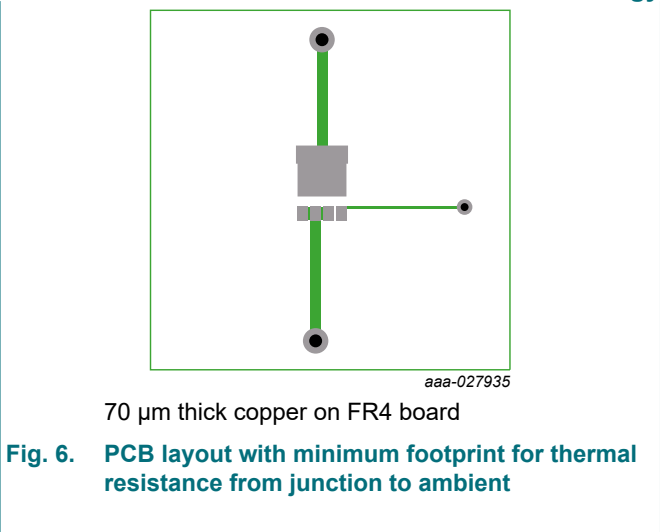
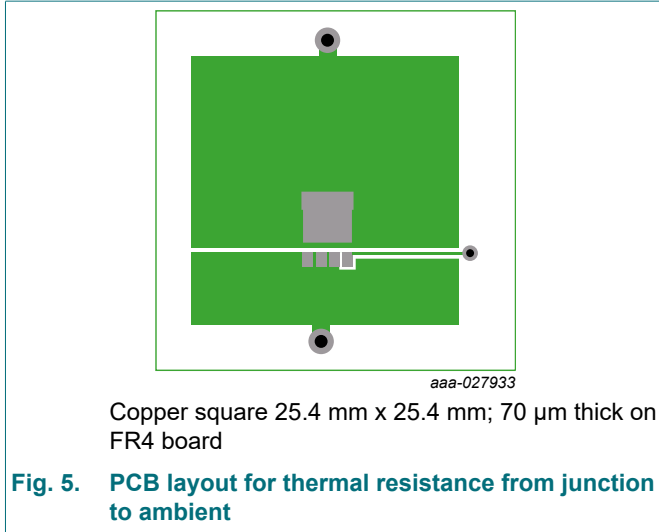
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4 | - | 0.33 | 0.45 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 5 | - | 42 | - | K/W |
| | | Fig. 6 | - | 85 | - | K/W |



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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------------------------------|----------------------------------------------------------------------------------------------------------|------|------|------|------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$ | 40 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$ | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ | 1.35 | 1.7 | 2.05 | V |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$ | - | -4.9 | - | mV/K |
| I_{DSS} | drain leakage current | $V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | - | 1 | μA |
| | | $V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$ | - | 11 | - | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| | | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10 | - | 0.76 | 0.94 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C;$ Fig. 11 | - | - | 2 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10 | - | 0.97 | 1.2 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C;$ Fig. 11 | - | - | 2.6 | mΩ |
| R_G | gate resistance | $f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ | 0.4 | 1 | 2.6 | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13 | - | 54 | 76 | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 12; Fig. 13 | - | 120 | 168 | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 63 | - | nC |
| Q_{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13 | - | 20 | 30 | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | - | 12 | 18 | nC |

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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|---------------------------|-----------------------------------|------------------------------------------------------------------------------------------------------------------------|-----|------|-------|------|----|
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 8 | 12 | nC | |
| Q_{GD} | gate-drain charge | | - | 13 | 26 | nC | |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25\text{ A}$; $V_{DS} = 20\text{ V}$; Fig. 12; Fig. 13 | - | 2.7 | - | V | |
| C_{iss} | input capacitance | $V_{DS} = 20\text{ V}$; $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$; Fig. 14 | - | 9052 | 12673 | pF | |
| C_{oss} | output capacitance | | - | 1702 | 2383 | pF | |
| C_{rss} | reverse transfer capacitance | | - | 347 | 764 | pF | |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 20\text{ V}$; $R_L = 0.8\text{ }\Omega$; $V_{GS} = 4.5\text{ V}$; $R_{G(ext)} = 5\text{ }\Omega$ | - | 45 | - | ns | |
| t_r | rise time | | - | 46 | - | ns | |
| $t_{d(off)}$ | turn-off delay time | | - | 59 | - | ns | |
| t_f | fall time | | - | 33 | - | ns | |
| Q_{oss} | output charge | $V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$ | - | 57 | - | nC | |
| Source-drain diode | | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; Fig. 15 | - | 0.76 | 1.2 | V | |
| t_{rr} | reverse recovery time | $I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$; Fig. 16 | - | 45 | - | ns | |
| Q_r | recovered charge | | [1] | - | 53 | - | nC |
| t_a | reverse recovery rise time | | - | - | 25 | - | ns |
| t_b | reverse recovery fall time | | - | - | 19 | - | ns |

[1] includes capacitive recovery

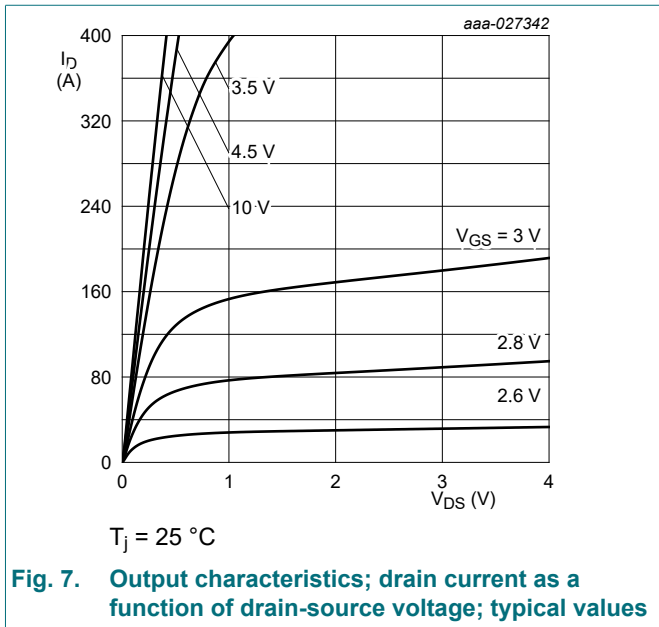


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

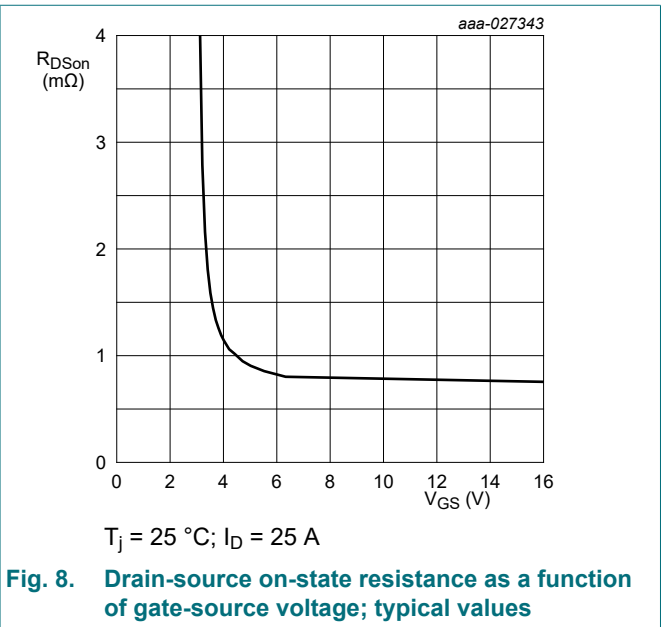


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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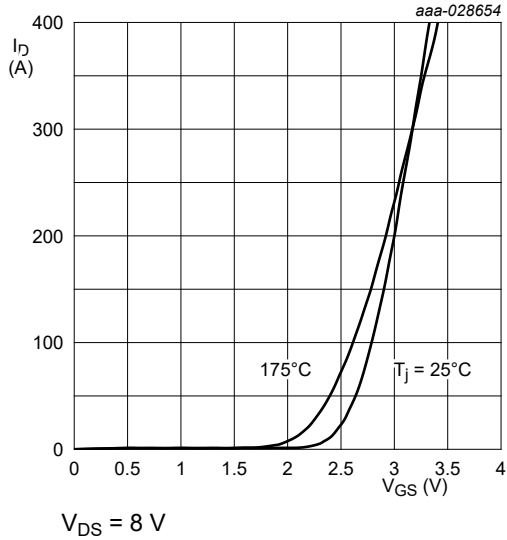


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

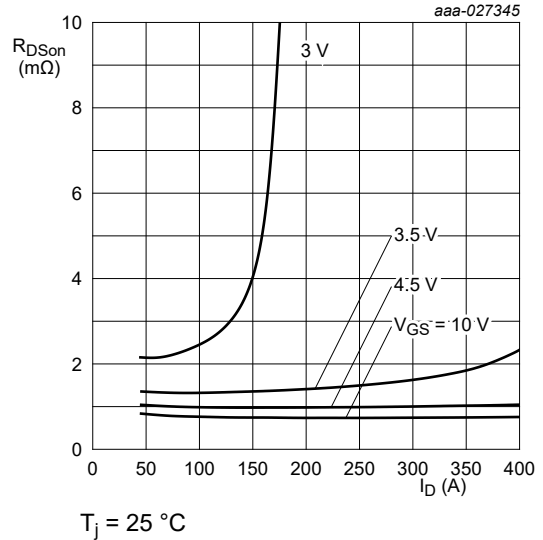


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

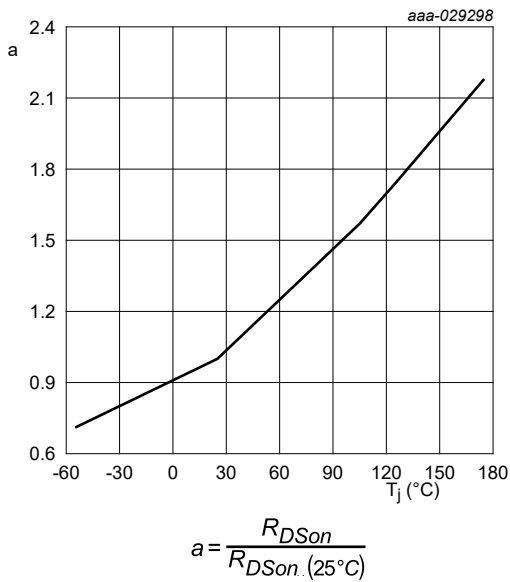


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

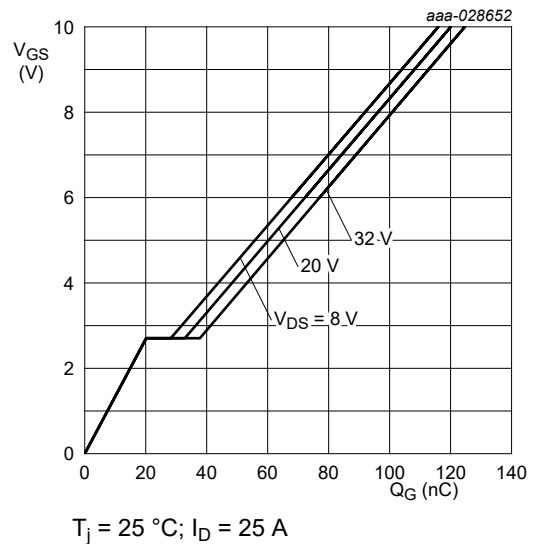


Fig. 12. Gate-source voltage as a function of gate charge; typical values

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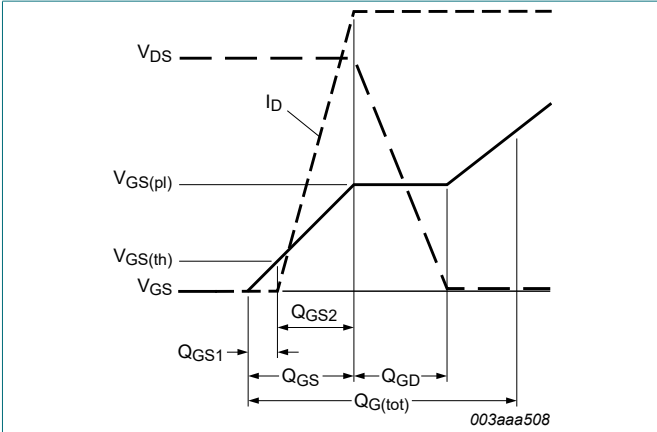
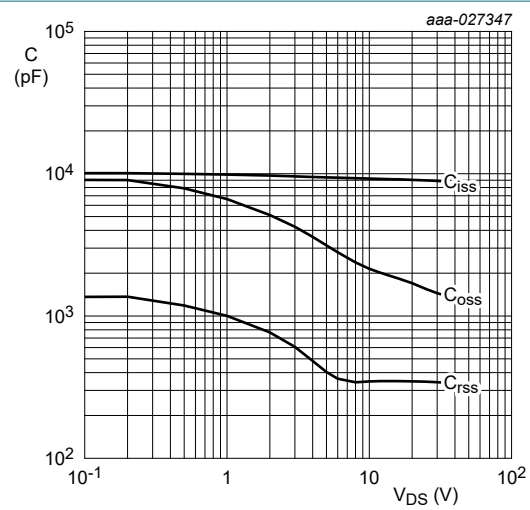
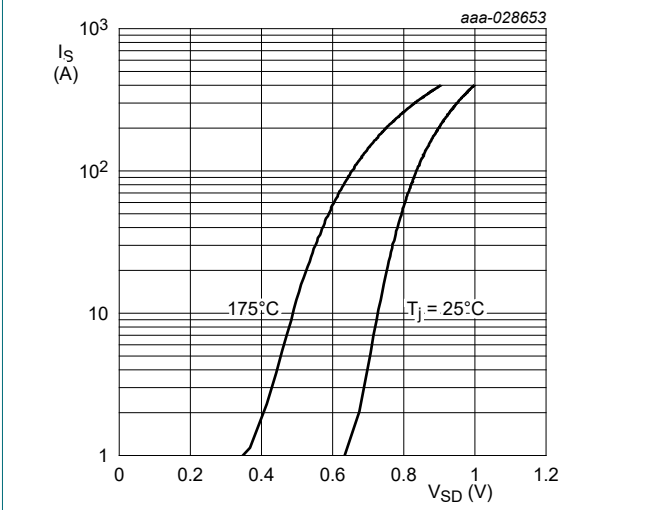


Fig. 13. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

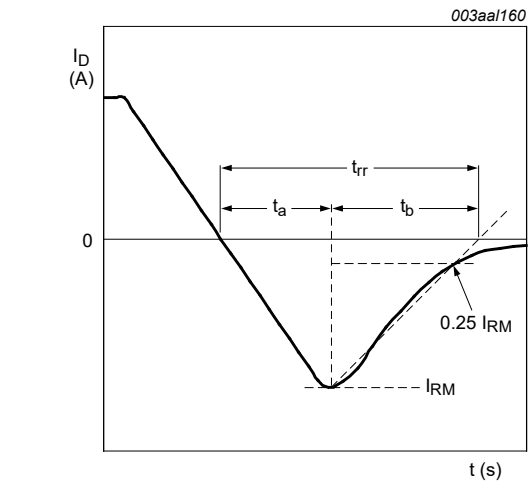


Fig. 16. Reverse recovery timing definition

11. Package outline

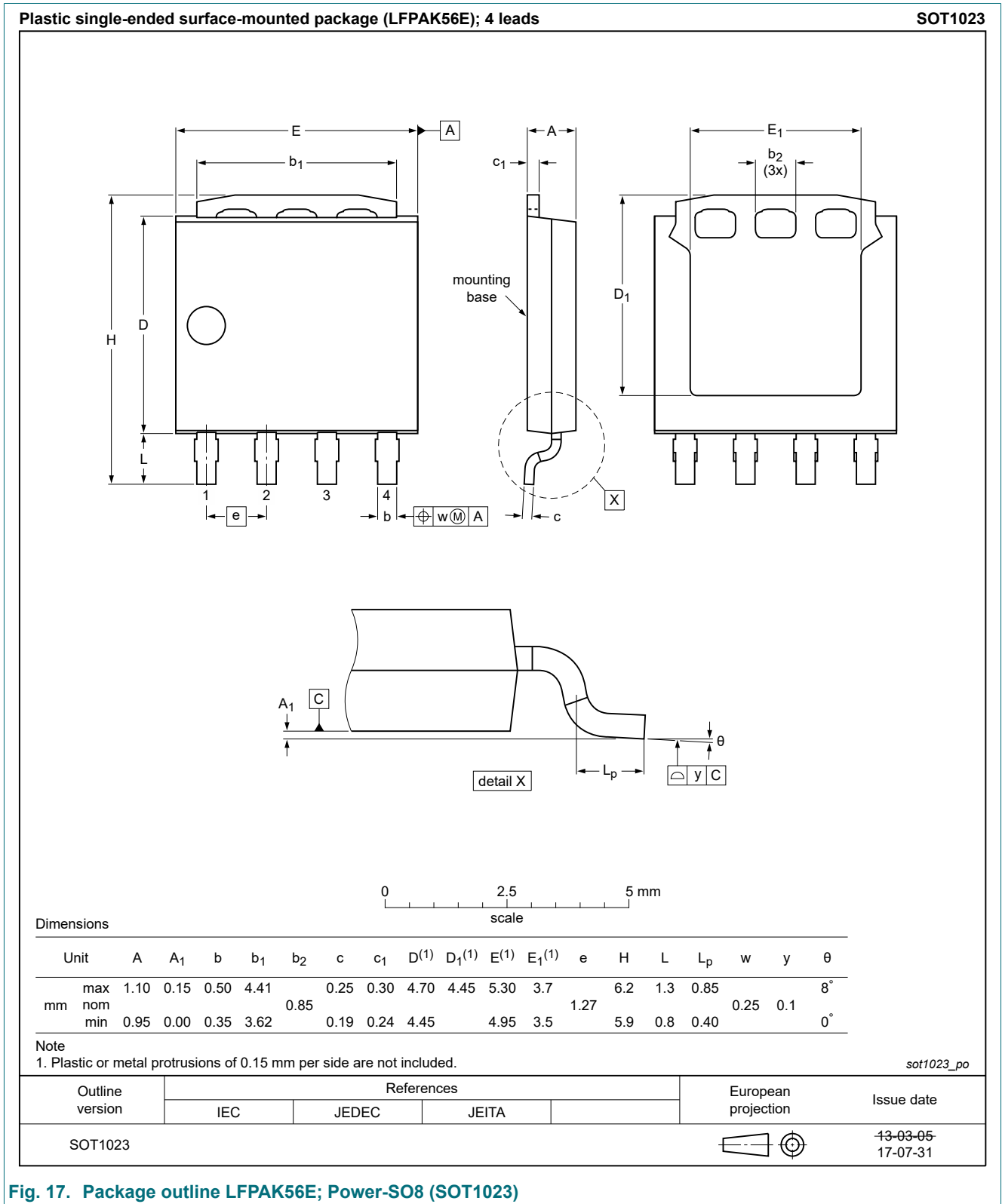


Fig. 17. Package outline LPAK56E; Power-SO8 (SOT1023)

12. Soldering

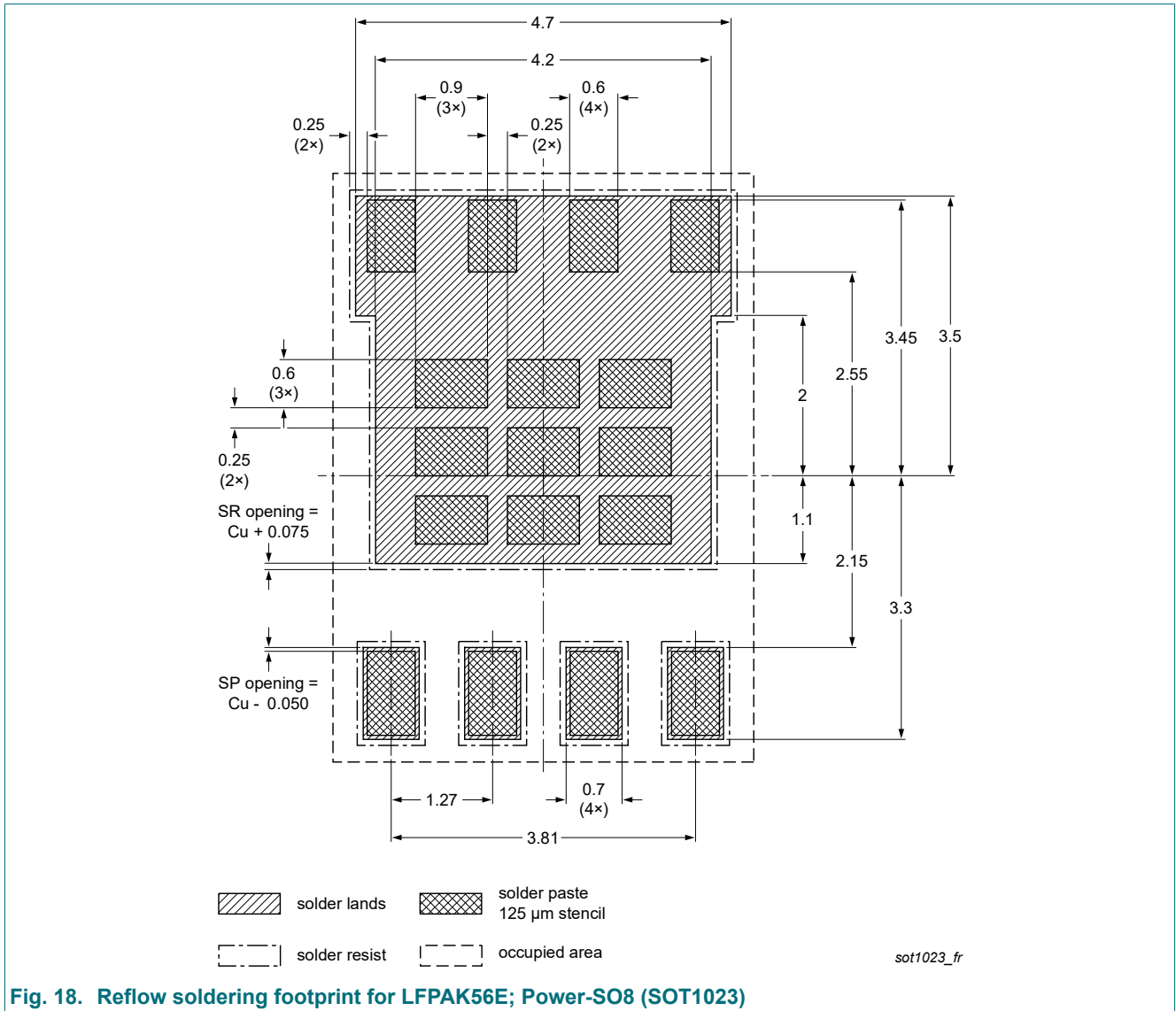


Fig. 18. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)

N-channel 40 V, 0.94 mΩ, 300 A logic level MOSFET in LPAK56E using NextPower-S3 Schottky-Plus technology

13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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